

PHOTOTRANSISTOR

Industry Standard Single Channel 6 Pin DIP Optocoupler

DEVICE TYPES

Part No.	CTR, % Min.	Part No.	CTR % Min.
4N25	20	MCT2	20
4N26	20	MCT2E	20
4N27	10	MCT270	50
4N28	10	MCT271	45-90
4N35	100	MCT272	75-150
4N36	100	MCT273	125-250
4N37	100	MCT274	225-400
4N38	10	MCT275	70-90
H11A1	50	MCT276	15-60
H11A2	20	MCT277	100
H11A3	20		
H11A4	10		
H11A5	30		

FEATURES

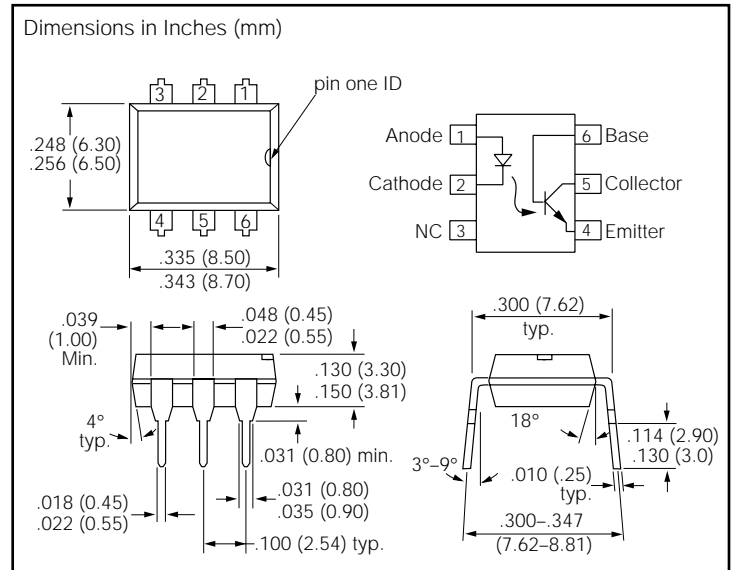
- Interfaces with Common Logic Families
- Input-output Coupling Capacitance < 0.5 pF
- Industry Standard Dual-in-line 6-pin Package
- Field Effect Stable by TRIOS
- 5300 VAC_{RMS} Isolation Test Voltage
- Recognized under Underwriters Laboratory File #E52744
- VDE #0884 Approval Available with Option -001

APPLICATIONS

- AC Mains Detection
- Reed Relay Driving
- Switch Mode Power Supply Feedback
- Telephone Ring Detection
- Logic Ground Isolation
- Logic Coupling with High Frequency Noise Rejection

Notes:

1. TRIOS=TRansparent IOn Shield
2. Designing with data sheet is covered in Application Note 45, Application Notes section of Data Book.



DESCRIPTION

This data sheet presents five families of Siemens Industry Standard Single Channel Phototransistor Couplers. These families include the 4N25/26/27/28 types, the 4N35/36/37/38 couplers, the H11A1/A2/A3/A4/A5, the MCT2/2E, and MCT270/271/272/273/274/275/276/277 devices. Each optocoupler consists of Gallium Arsenide infrared LED and a silicon NPN phototransistor.

All couplers are Underwriters Laboratories (UL) listed to comply with a 7500 V_{AC(PK)} Isolation Test Voltage. This isolation performance is accomplished through Siemens double molding isolation manufacturing process. Compliance to VDE 0884 partial discharge isolation specification is available for these families by ordering option -001. Phototransistor gain stability, in the presence of high isolation voltages, is insured by incorporating a TRansparent IOn Shield (TRIOS) on the phototransistor substrate. These isolation processes and the Siemens IS09001 Quality program results in the highest isolation performance available for a commercial plastic phototransistor optocoupler.

The devices are available in lead formed configuration suitable for surface mounting and are available either on tape and reel, or in standard tube shipping containers.

Maximum Ratings $T_A=25^\circ\text{C}$

Emitter

Reverse Voltage	6 V
Forward Current	60 mA
Surge Current ($t \leq 10 \mu\text{s}$)	2.5 A
Power Dissipation	100 mW

Detector

Collector-Emitter Breakdown Voltage	70 V
Emitter-Base Breakdown Voltage	7 V
Collector Current	50 mA
Collector Current ($t < 1 \text{ ms}$)	100 mA
Power Dissipation	150 mW

Package

Isolation Test Voltage	5300 VAC _{RMS}
Creepage	$\geq 7 \text{ mm}$
Clearance	$\geq 7 \text{ mm}$
Isolation Thickness between Emitter and Detector	$\geq 0.4 \text{ mm}$
Comparative Tracking Index per DIN IEC 112/VDE0303, part 1	175
Isolation Resistance	
$V_{IO}=500 \text{ V}, T_A=25^\circ\text{C}$	$10^{12} \Omega$
$V_{IO}=500 \text{ V}, T_A=100^\circ\text{C}$	$10^{11} \Omega$
Storage Temperature	-55°C to $+150^\circ\text{C}$
Operating Temperature	-55°C to $+100^\circ\text{C}$
Junction Temperature	100°C
Soldering Temperature (max. 10 s, dip soldering: distance to seating plane $\geq 1.5 \text{ mm}$)	
	260°C

4N25/26/27/28—Characteristics $T_A=25^\circ\text{C}$

Emitter		Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage*		V_F		1.3	1.5	V	$I_F=50 \text{ mA}$
Reverse Current*		I_R		0.1	100	μA	$V_R=3.0 \text{ V}$
Capacitance		C_0		25		pF	$V_R=0$
Detector							
Breakdown Voltage*	Collector-Emitter	BV_{CEO}	30			V	$I_C=1 \text{ mA}$
	Emitter-Collector	BV_{ECO}	7				$I_E=100 \mu\text{A}$
	Collector-Base	BV_{CBO}	70				$I_C=100 \mu\text{A}$
$I_{CEO}(\text{dark})^*$	4N25/26/27 4N28			5 10	50 100	nA	$V_{CE}=10 \text{ V}$, (base open)
$I_{CBO}(\text{dark})^*$				2	20	nA	$V_{CB}=10 \text{ V}$, (emitter open)
Capacitance, Collector-Emitter		C_{CE}		6		pF	$V_{CE}=0$
Package							
DC Current Transfer Ratio*	4N25/26	CTR	20	50		%	$V_{CE}=10 \text{ V}$, $I_F=10 \text{ mA}$
	4N27/28		10	30			
Isolation Voltage*	4N25	V_{IO}	2500			V	Peak, 60 Hz
	4N26/27		1500				
	4N28		500				
Saturation Voltage, Collector-Emitter		$V_{CE(\text{sat})}$			0.5	V	$I_{CE}=2.0 \text{ mA}$, $I_F=50 \text{ mA}$
Resistance, Input to Output*		R_{IO}	100			G Ω	$V_{IO}=500 \text{ V}$
Coupling Capacitance		C_{IO}		0.5		pF	$f=1 \text{ MHz}$
Rise and Fall Times		t_R, t_F		2		μs	$I_F=10 \text{ mA}$ $V_{CE}=10 \text{ V}$, $R_E=100 \Omega$

* Indicates JEDEC registered values

4N35/36/37/38—Characteristics $T_A=25^\circ\text{C}$

Emitter		Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage*		V_F	0.9	1.3	1.5 1.7	V	$I_F=10\text{ mA}$ $I_F=10\text{ mA}, T_A=-55^\circ\text{C}$
Reverse Current*		I_R		0.1	10	μA	$V_R=6.0\text{ V}$
Capacitance		C_O		25		pF	$V_R=0, f=1\text{ MHz}$
Detector							
Breakdown Voltage, Collector-Emitter*		4N35/36/37 4N38	BV_{CEO}	30 80		V	$I_C=1\text{ mA}$
Breakdown Voltage, Emitter-Collector*			BV_{ECO}	7		V	$I_E=100\ \mu\text{A}$
Breakdown Voltage, Collector-Base*		4N35/36/37 4N38	BV_{CBO}	70 80		V	$I_C=100\ \mu\text{A}, I_B=1\ \mu\text{A}$
Leakage Current, Collector-Emitter*		4N35/36/37 4N38	I_{CEO}		5 50	nA	$V_{CE}=10\text{ V}, I_F=0$ $V_{CE}=60\text{ V}, I_F=0$
Leakage Current, Collector-Emitter*		4N35/36/37 4N38	I_{CEO}		500 6	μA	$V_{CE}=30\text{ V}, I_F=0, T_A=100^\circ\text{C}$ $V_{CE}=60\text{ V}, I_F=0, T_A=100^\circ\text{C}$
Capacitance, Collector-Emitter			C_{CE}	6		pF	$V_{CE}=0$
Package							
DC Current Transfer Ratio*		4N35/36/37 4N38	CTR	100 20		%	$V_{CE}=10\text{ V}, I_F=10\text{ mA},$ $V_{CE}=1\text{ V}, I_F=20\text{ mA}$
DC Current Transfer Ratio*		4N35/36/37 4N38	CTR	40 30	50	%	$V_{CE}=10\text{ V}, I_F=10\text{ mA},$ $T_A=-55\text{ to }100^\circ\text{C}$
Resistance, Input to Output*			R_{IO}	10^{11}		W	$V_{IO}=500\text{ V}$
Coupling Capacitance*			C_{IO}	0.5		pF	$f=1\text{ MHz}$
Switching Time*			t_{ON}, t_{OFF}	10		μs	$I_C=2\text{ mA}, R_E=100\ \Omega, V_{CC}=10\text{ V}$

* Indicates JEDEC registered value

H11A1 through H11A5—Characteristics $T_A=25^\circ\text{C}$

Emitter		Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage		H11A1–H11A4 H11A5	V_F		1.1 1.7	V	$I_F=10\text{ mA}$
Reverse Current			I_R		10	μA	$V_R=3\text{ V}$
Capacitance			C_0	50		pF	$V_R=0, f=1\text{ MHz}$
Detector							
Breakdown Voltage, Collector-Emitter			BV_{CEO}	30		V	$I_C=1\text{ mA}, I_F=0\text{ mA}$
Breakdown Voltage, Emitter-Collector			BV_{ECO}	7		V	$I_E=100\ \mu\text{A}, I_F=0\text{ mA}$
Breakdown Voltage, Collector-Base			BV_{CBO}	70		V	$I_C=10\ \mu\text{A}, I_F=0\text{ mA}$
Leakage Current, Collector-Emitter			I_{CEO}	5	50	nA	$V_{CE}=10\text{ V}, I_F=0\text{ mA}$
Capacitance, Collector-Emitter			C_{CE}	6		pF	$V_{CE}=0$
Package							
DC Current Transfer Ratio		H11A1 H11A2/3 H11A4 H11A5	CTR	50 20 10 30		%	$V_{CE}=10\text{ V}, I_F=10\text{ mA}$
Saturation Voltage, Collector-Emitter			V_{CESat}		0.4	V	$I_{CE}=0.5\text{ mA}, I_F=10\text{ mA}$
Capacitance, Input to Output			C_{IO}	0.5		pF	
Switching Time			t_{ON}, t_{OFF}	3.0		μs	$I_C=2\text{ mA}, R_E=100\ \Omega, V_{CE}=10\text{ V}$

MCT2/MCT2E—Characteristics $T_A=25^\circ\text{C}$

Emitter		Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage		V_F		1.1	1.5	V	$I_F=20\text{ mA}$
Reverse Current		I_R			10	μA	$V_R=3\text{ V}$
Capacitance		C_0		25		pF	$V_R=0, f=1\text{ MHz}$
Detector							
Breakdown Voltage	Collector-Emitter	BV_{CEO}	30			V	$I_C=1\text{ mA}, I_F=0\text{ mA}$
	Emitter-Collector	BV_{ECO}	7				$I_E=100\ \mu\text{A}, I_F=0\text{ mA}$
	Collector-Base	BV_{CBO}	70				$I_C=10\ \mu\text{A}, I_F=0\text{ mA}$
Leakage Current	Collector-Emitter	I_{CBO}		5	50	nA	$V_{CE}=10\text{ V}, I_F=0$
	Collector-Base	I_{CBO}			20		
Capacitance, Collector-Emitter		C_{CE}		10		pF	$V_{CE}=0$
Package							
DC Current Transfer Ratio		CTR	20	60		%	$V_{CE}=10\text{ V}, I_F=10\text{ mA}$
Capacitance, Input to Output		C_{IO}		0.5		pF	
Resistance, Input to Output		R_{IO}		100		$\text{G}\Omega$	
Switching Time		t_{ON}, t_{OFF}		3.0		μs	$I_C=2\text{ mA}, R_E=100\ \Omega, V_{CE}=10\text{ V}$

MCT270 through MCT277—Characteristics $T_A=25^\circ\text{C}$

Emitter		Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage		V_F			1.5	V	$I_F=20\text{ mA}$
Reverse Current		I_R			10	μA	$V_R=3\text{ V}$
Capacitance		C_0		25		pF	$V_R=0, f=1\text{ MHz}$
Detector							
Breakdown Voltage	Collector-Emitter	BV_{CEO}	30			V	$I_C=10\ \mu\text{A}, I_F=0\text{ mA}$
	Emitter-Collector	BV_{ECO}	7				$I_E=10\ \mu\text{A}, I_F=0\text{ mA}$
	Collector-Base	BV_{CBO}	70				$I_C=10\ \mu\text{A}, I_F=0\text{ mA}$
Leakage Current, Collector-Emitter		I_{CEO}			50	nA	$V_{CE}=10\text{ V}, I_F=0\text{ mA}$
Package							
DC Current Transfer Ratio	MCT270	CTR	50			%	$V_{CE}=10\text{ V}, I_F=10\text{ mA}$
	MCT271				90		
	MCT272				150		
	MCT273				250		
	MCT274				400		
	MCT275				210		
	MCT276				60		
	MCT277				100		
Current Transfer Ratio, Collector-Emitter	MCT271-276	CTR_{CE}	12.5			%	$V_{CE}=0.4\text{ V}, I_F=16\text{ mA}$
	MCT277				40		
Collector-Emitter Saturation Voltage		V_{CEsat}			0.4	V	$I_{CE}=2\text{ mA}, I_F=16\text{ mA}$
Capacitance, Input to Output		C_{IO}		0.5		pF	
Resistance, Input to Output		R_{IO}		10^{12}		W	$V_{IO}=500\text{ VDC}$
Switching Time	MCT270/272	t_{ON}, t_{OFF}			10	μs	$I_C=2\text{ mA}, R_E=100\ \Omega, V_{CE}=5\text{ V}$
	MCT271				7		
	MCT273				20		
	MCT274				25		
	MCT275/277				15		
	MCT276				3.5		

Figure 1. Forward voltage vs. forward current

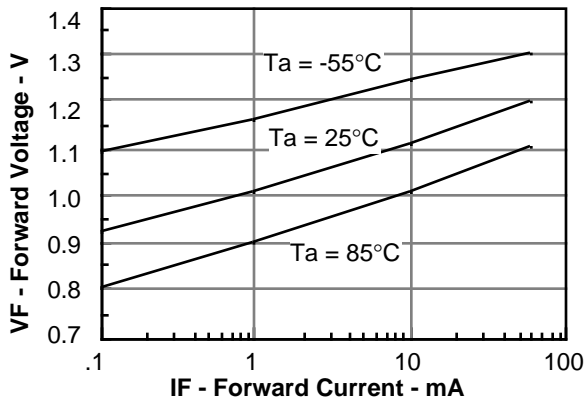


Figure 2. Normalized non-saturated and saturated CTR, $T_A=25^\circ\text{C}$ vs. LED current

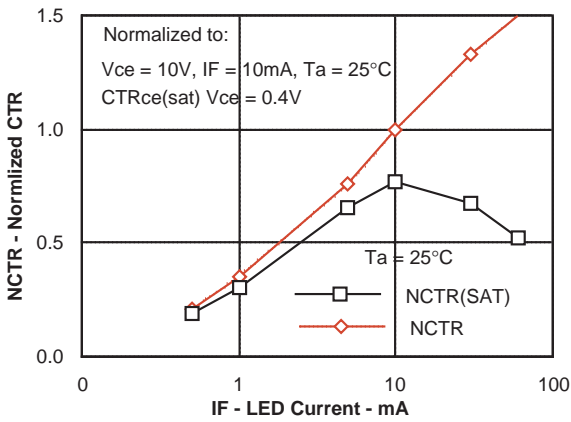


Figure 3. Normalized non-saturated and saturated CTR, $T_A=50^\circ\text{C}$ vs. LED current

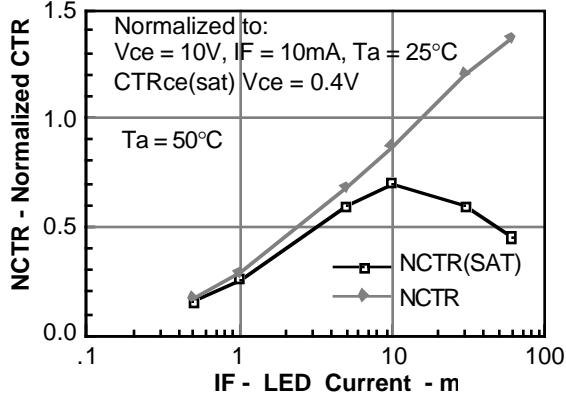


Figure 4. Normalized non-saturated and saturated CTR, $T_A=70^\circ\text{C}$ vs. LED current

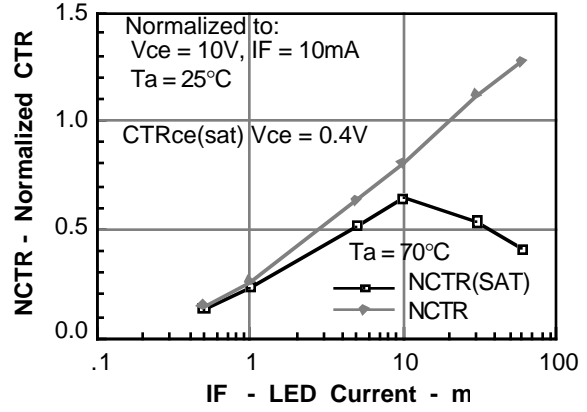


Figure 5. Normalized non-saturated and saturated CTR, $T_A=85^\circ\text{C}$ vs. LED current

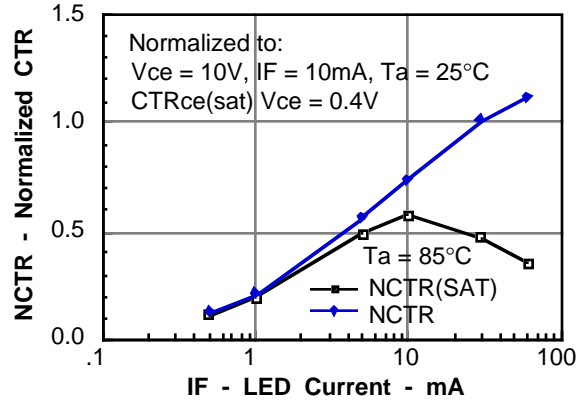


Figure 6. Collector-emitter current vs. temperature and LED current

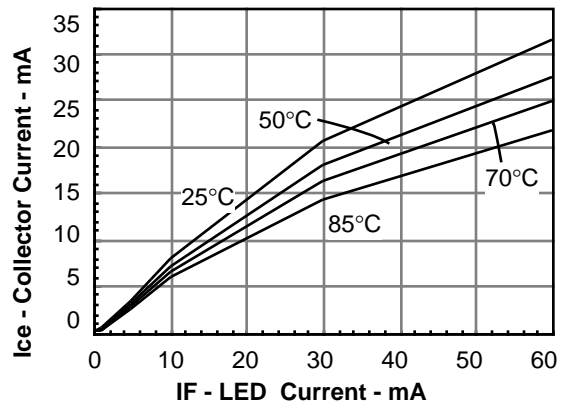


Figure 7. Collector-emitter leakage current vs. temp.

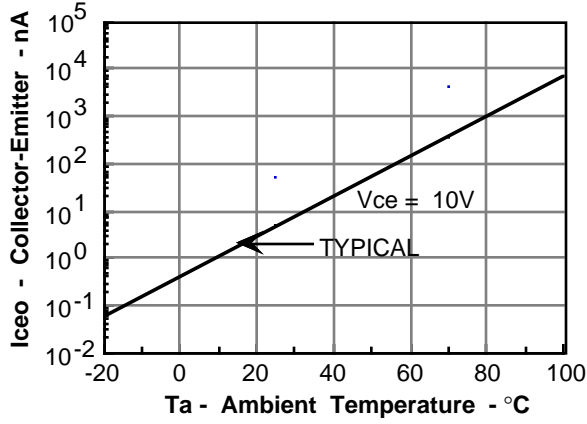


Figure 8. Normalized CTRcb vs. LED current and temp.

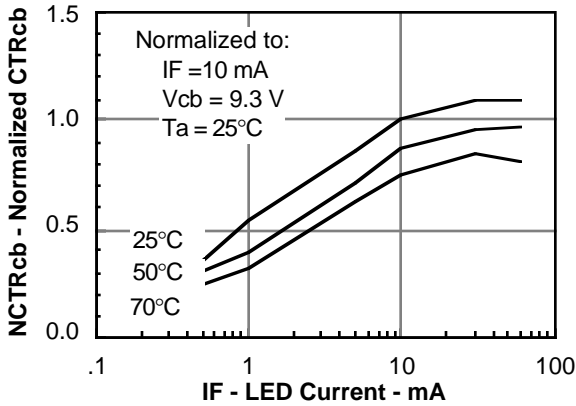


Figure 9. Normalized photocurrent vs. If and temperature

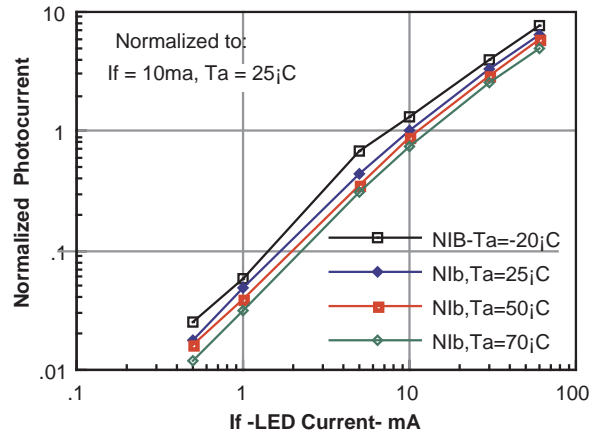


Figure 13. Switching timing

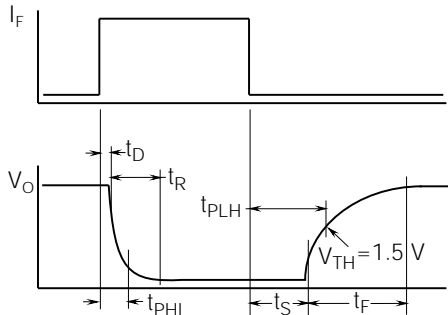


Figure 10. Normalized non-saturated HFE vs. base current and temperature

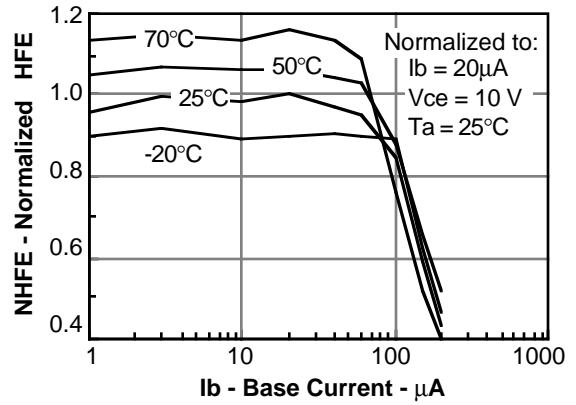


Figure 11. Normalized HFE vs. base current and temp.

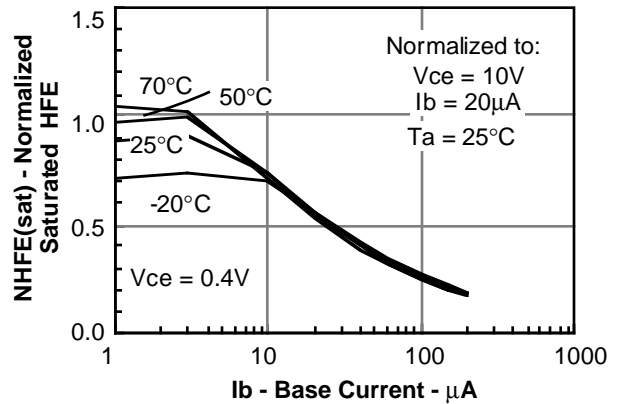


Figure 12. Propagation delay vs. collector load resistor

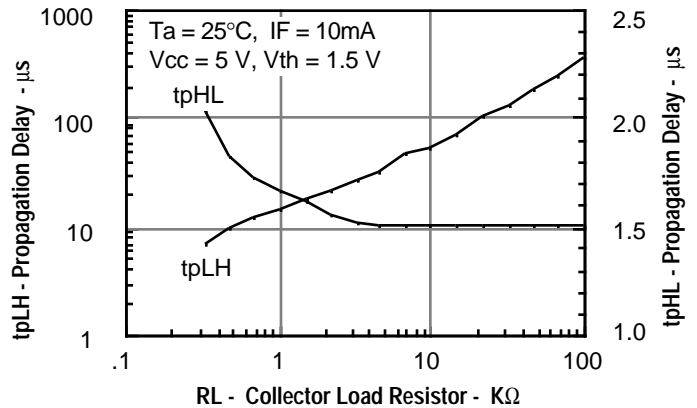


Figure 14. Switching schematic

